



MMBT3906FN3

PNP GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volt **POWER** 250 mWatt

DFN 3L Unit : inch(mm)

FEATURES

- PNP epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = -40V$
- Collector current $I_C = -200mA$
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. . (Halogen Free)

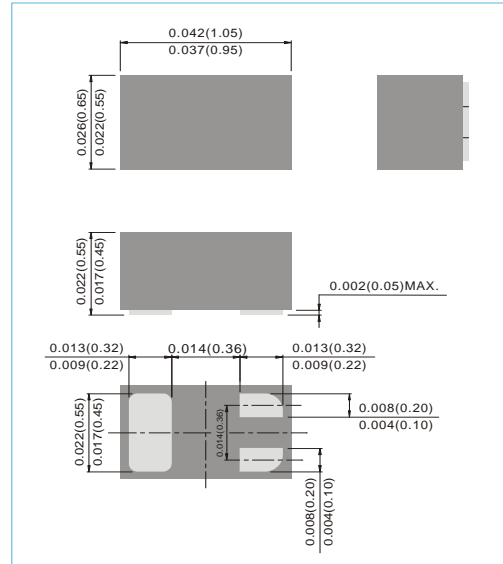
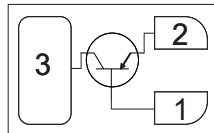
MECHANICAL DATA

Case: DFN 3L, Plastic

Terminals: Solderable per MIL-STD-750, Method 2026

Approx weight: 0.00004 ounce, 0.0011 gram

Marking: AD



ABSOLUTE RATINGS

Parameter	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	-40	V
Collector - Base Voltage	V_{CBO}	-40	V
Emitter - Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-200	mA

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	250	mW
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	500	$^{\circ}C/W$
Junction Temperature	T_J	-55 to +150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}C$

Note 1: Transistor mounted on FR-4 board 70 x 60 x 1mm.



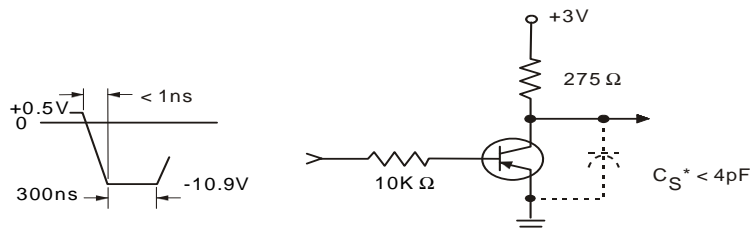
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ELECTRICAL CHARACTERISTICS $T_A=25^\circ\text{C}$

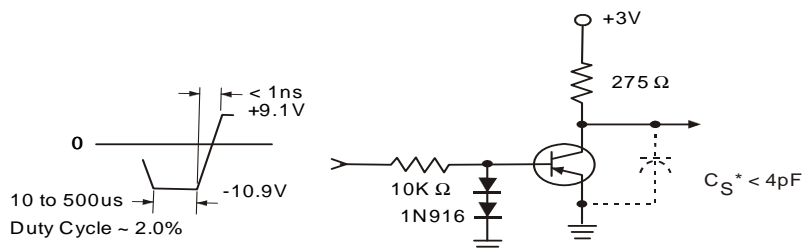
Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-40	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5	-	-	V
Base Cutoff Current	I_{BL}	$V_{CE}=-30\text{V}, V_{EB}=-3\text{V}$	-	-	-50	nA
Collector Cutoff Current	I_{CEX}	$V_{CE}=-30\text{V}, V_{EB}=-3\text{V}$	-	-	-50	nA
DC Current Gain (Note 2)	h_{FE}	$I_C=-0.1\text{mA}, V_{CE}=-1\text{V}$	60	-	-	-
		$I_C=-1\text{mA}, V_{CE}=-1\text{V}$	80	-	-	
		$I_C=-10\text{mA}, V_{CE}=-1\text{V}$	100	-	300	
		$I_C=-50\text{mA}, V_{CE}=-1\text{V}$	60	-	-	
		$I_C=-100\text{mA}, V_{CE}=-1\text{V}$	30	-	-	
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$ $I_C=-50\text{mA}, I_B=-5\text{mA}$	-	-	-0.25 -0.4	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$ $I_C=-50\text{mA}, I_B=-5\text{mA}$	-0.65 -	-	-0.85 -0.95	V
Collector - Base Capacitance	C_{CBO}	$V_{CB}=-5\text{V}, I_E=0, f=1\text{MHz}$	-	-	4.5	pF
Emitter - Base Capacitance	C_{EBO}	$V_{EB}=-0.5\text{V}, I_C=0, f=1\text{MHz}$	-	-	10	pF
Delay Time	t_d	$V_{CC}=-3\text{V}, V_{BE}=-0.5\text{V}, I_C=-10\text{mA}, I_B=-1\text{mA}$	-	-	35	ns
Rise Time	t_r	$V_{CC}=-3\text{V}, V_{BE}=-0.5\text{V}, I_C=-10\text{mA}, I_B=-1\text{mA}$	-	-	35	ns
Storage Time	t_s	$V_{CC}=-3\text{V}, I_C=-10\text{mA}, I_{B1}=I_{B2}=-1\text{mA}$	-	-	225	ns
Fall Time	t_f	$V_{CC}=-3\text{V}, I_C=-10\text{mA}, I_{B1}=I_{B2}=-1\text{mA}$	-	-	75	ns
Current Gain-Bandwidth Product	f_T	$I_C=-10\text{mA}, V_{CE}=-20\text{V}, f=100\text{MHz}$	250	-	-	MHz

Note 2: Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS



Delay and Rise Time Equivalent Test Circuit



Storage and Fall Time Equivalent Test Circuit



ELECTRICAL CHARACTERISTICS CURVE

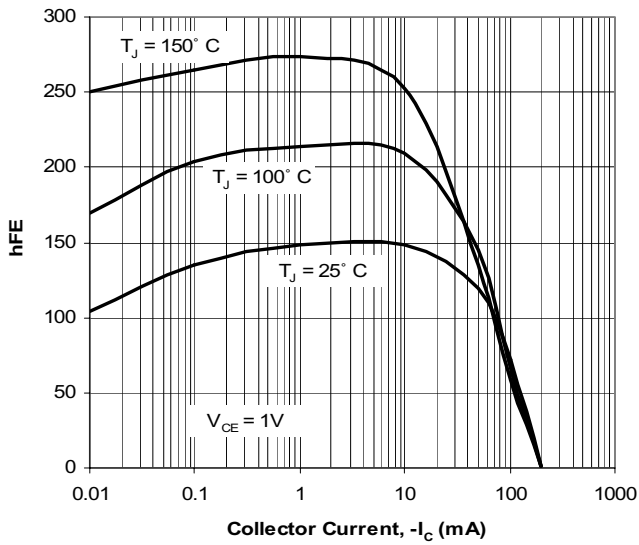


Fig. 1. Typical h_{FE} vs. Collector Current

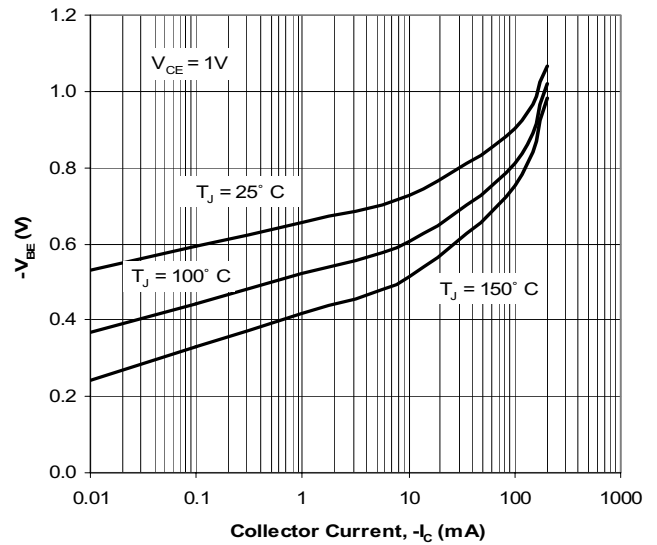


Fig. 2. Typical V_{BE} vs. Collector Current

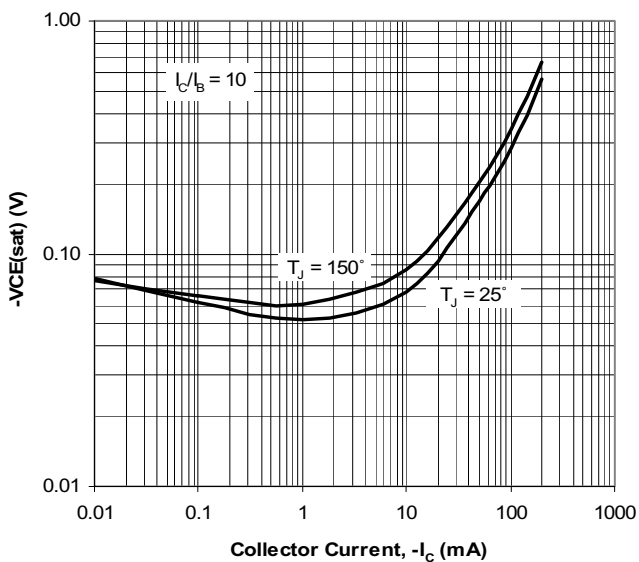


Fig. 3. Typical $V_{CE(sat)}$ vs. Collector Current

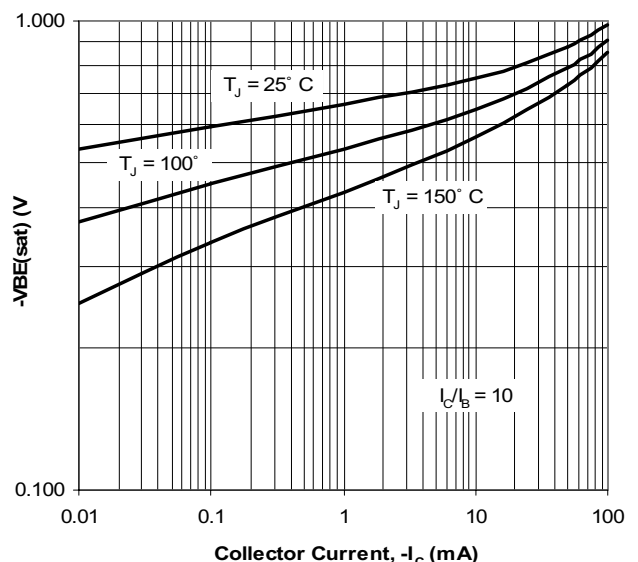


Fig. 4. Typical $V_{BE(sat)}$ vs. Collector Current

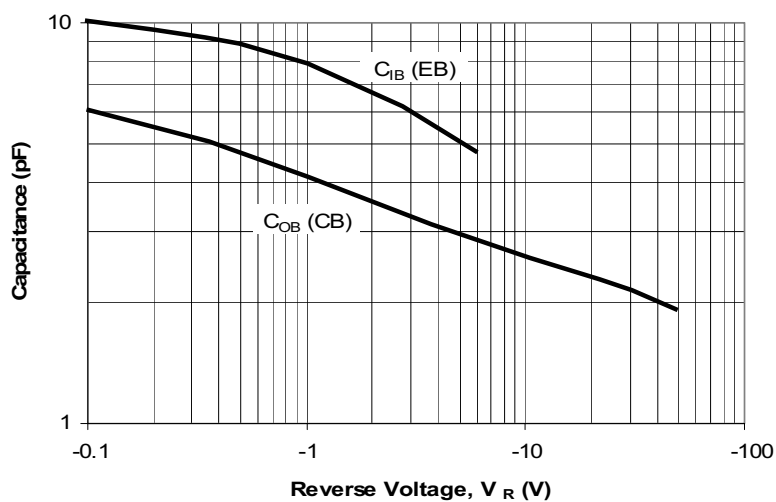
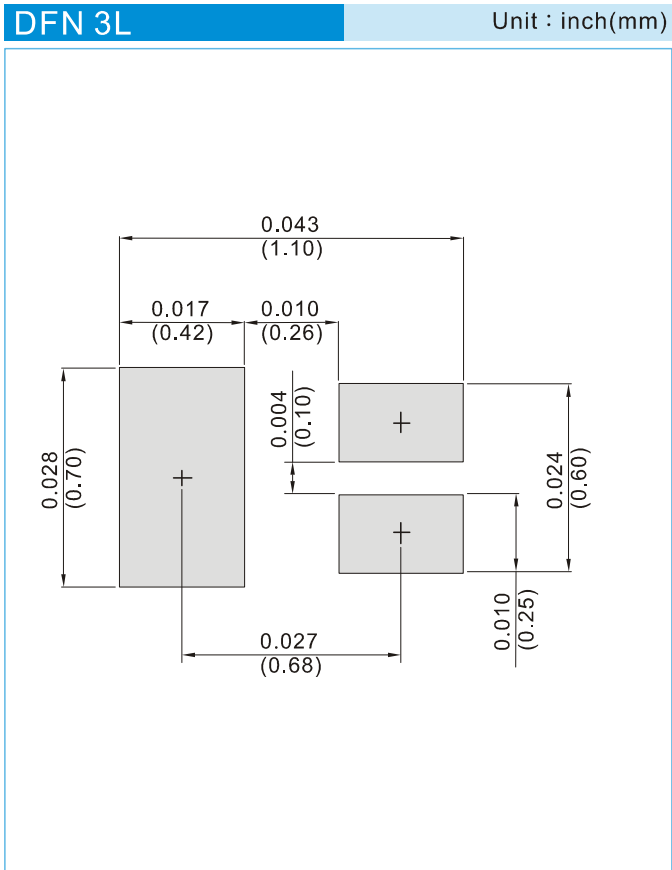


Fig. 5. Typical Capacitances vs. Reverse Voltage



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
T/R - 8K per 7" plastic Reel



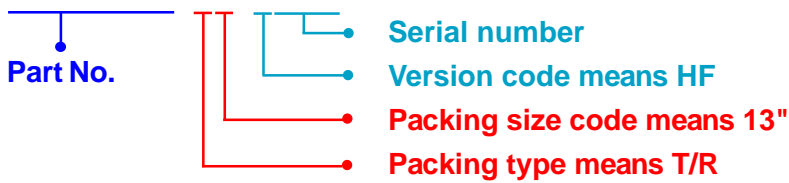
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Part No_packing code_Version

MMBT3906FN3_R1_00001

For example :

RB500V-40_R2_00001



Packing Code XX				Version Code XXXXX		
Packing type	1 st Code	Packing size code	2 nd Code	HF or RoHS	1 st Code	2 nd ~5 th Code
Tape and Ammunition Box (T/B)	A	N/A	0	HF	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS	1	serial number
Bulk Packing (B/P)	B	13"	2			
Tube Packing (T/P)	T	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			



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